

Features

- Low Noise Figure: 0.9 dB
- High OIP3: +28 dBm at 5 V, 60 mA bias
- High Gain: 21 dB
- Single Supply: +3 to +8 VDC
- Low Cost SOIC-8 Plastic Package
- Adjustable current: 20 to 80 mA with external resistor

Description

M/A-COM's MAALSS0025 is a high dynamic range, low noise GaAs MMIC amplifier in a low cost, surface mount package. It employs external input matching to obtain optimum noise figure performance and operating frequency flexibility.

The MAALSS0025 also features flexible biasing to control the current consumption vs. dynamic range trade-off. The MAALSS0025 can operate from any supply voltage in the 3 V to 8 V range. Its current can be controlled over a range of 20 mA to 80 mA with an external resistor.

The MAALSS0025 is ideally suited for use where low noise figure, high gain, high dynamic range, and low power consumption are required. Typical applications include receiver front ends in CDMA450 base stations. It is also useful as a gain block, buffer, driver, and IF amplifier in both fixed and portable cellular and 450 MHz ISM systems.

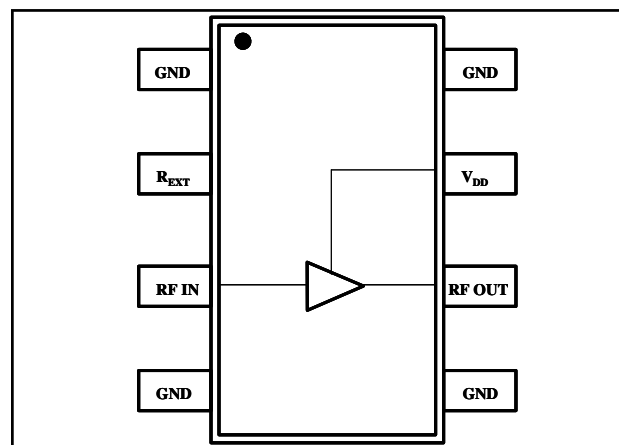
The MAALSS0025 is fabricated using a low-cost 0.5-micron gate length GaAs process. The process features full passivation for increased performance reliability.

Ordering Information^{1,2}

Part Number	Package
MAALSS0025	Bulk Packaging
MAALSS0025TR	1000 piece reel
MAALSS0025SMB	Sample Test Board

1. Reference Application Note M513 for reel size information.
2. All sample boards include 5 loose parts.

Functional Block Diagram



Pin Configuration

Pin No.	Pin Name	Description
1	GND	RF and DC Ground
2	R _{EXT}	External Current Control (optional)
3	RF IN	RF Input
4	GND	RF and DC Ground
5	GND	RF and DC Ground
6	RF OUT	RF Output
7	V _{DD}	Positive supply voltage
8	GND	RF and DC Ground

Absolute Maximum Ratings³

Parameter	Absolute Maximum
V _{DD}	+10 VDC
Input Power	+10 dBm
Current ⁴	120 mA
Channel Temperature ⁵	+150°C
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

3. Exceeding any one or combination of these limits may cause permanent damage to this device.
4. When pin #2 is used to increase current (see note 6).
5. Thermal resistance (θ_{jc}) = +88°C/W.

High Dynamic Range Low Noise Amplifier 400 - 500 MHz

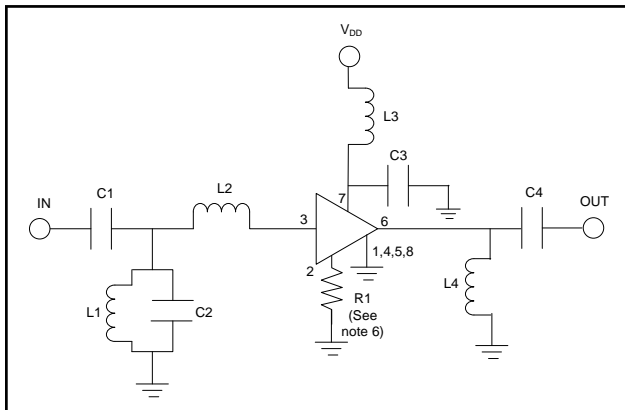
Rev. V1

Electrical Specifications: $T_A = +25^\circ\text{C}$, $Z_0 = 50 \Omega$, $F = 450 \text{ MHz}$, $P_{in} = -30 \text{ dBm}$

Parameter	Test Conditions	Units	Min	Typ	Max
Gain	5 V, 60 mA ⁶	dB	19	21	24
Noise Figure	5 V, 60 mA ⁶	dB	—	0.9	1.4
Input Return Loss	—	dB	—	9	—
Output Return Loss	—	dB	—	11	—
Output 1 dB Compression	5 V, 60 mA ³	dBm	—	16.5	—
Output IP3	5 V, 60 mA ³	dBm	—	28	—
Input IP3	5 V, 60 mA ³	dBm	3	7	—
Reverse Isolation	—	dB	—	34	—

6. Using external 15-ohm resistor. See functional schematic.

Functional Schematic



External Circuitry Parts List

Part	Value	Purpose
C1	100 pF	DC Block
C2	8 pF	Input Matching
C3	470 pF	Bypass
C4	4 pF	Output Matching
L1	22 nH	Input Matching
L2	43 nH	Input Matching
L3	12 nH	RF Choke
L4	11 nH	Output Matching
R1	15 Ohms	Optional current control ⁷ (see note 6)

7. Pin 2 allows use of an external resistor to ground for optional, higher current. For 20 mA operation, no resistor is used.

For $I_{DD} \sim 40 \text{ mA}$, $R_2 = 43 \text{ ohms}$;
 For $I_{DD} \sim 60 \text{ mA}$, $R_2 = 15 \text{ ohms}$;
 For $I_{DD} \sim 80 \text{ mA}$, $R_2 = 10 \text{ ohms}$.

Handling Procedures

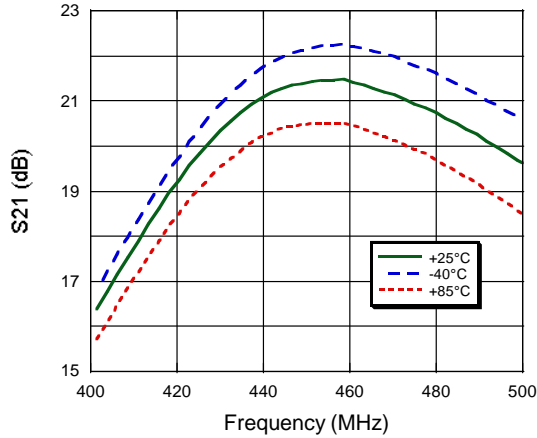
The following precautions should be observed to avoid damage:

Static Sensitivity

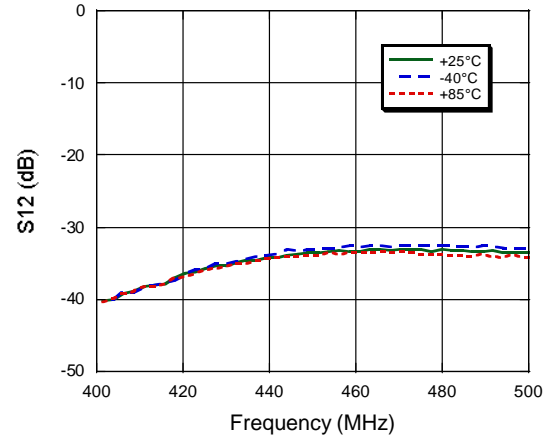
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Typical Performance Curves over Temperature

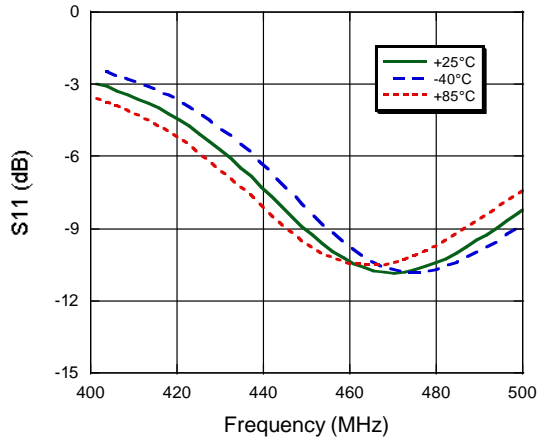
Gain



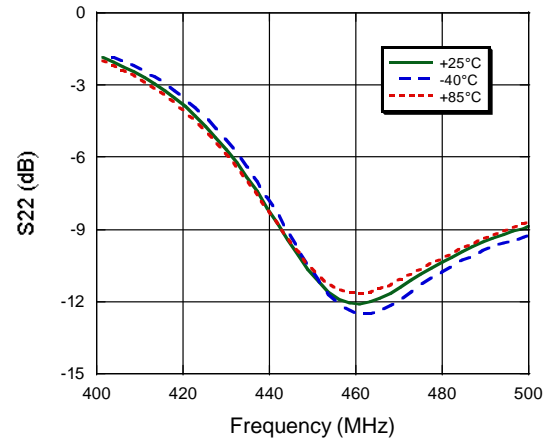
Reverse Isolation



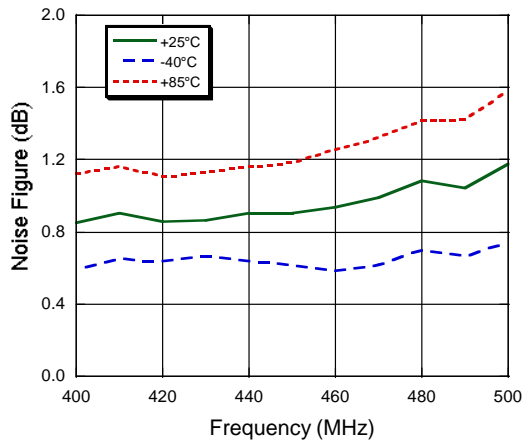
Input Return Loss



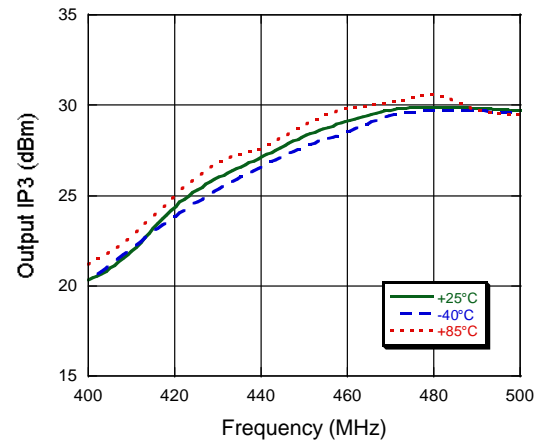
Output Return Loss



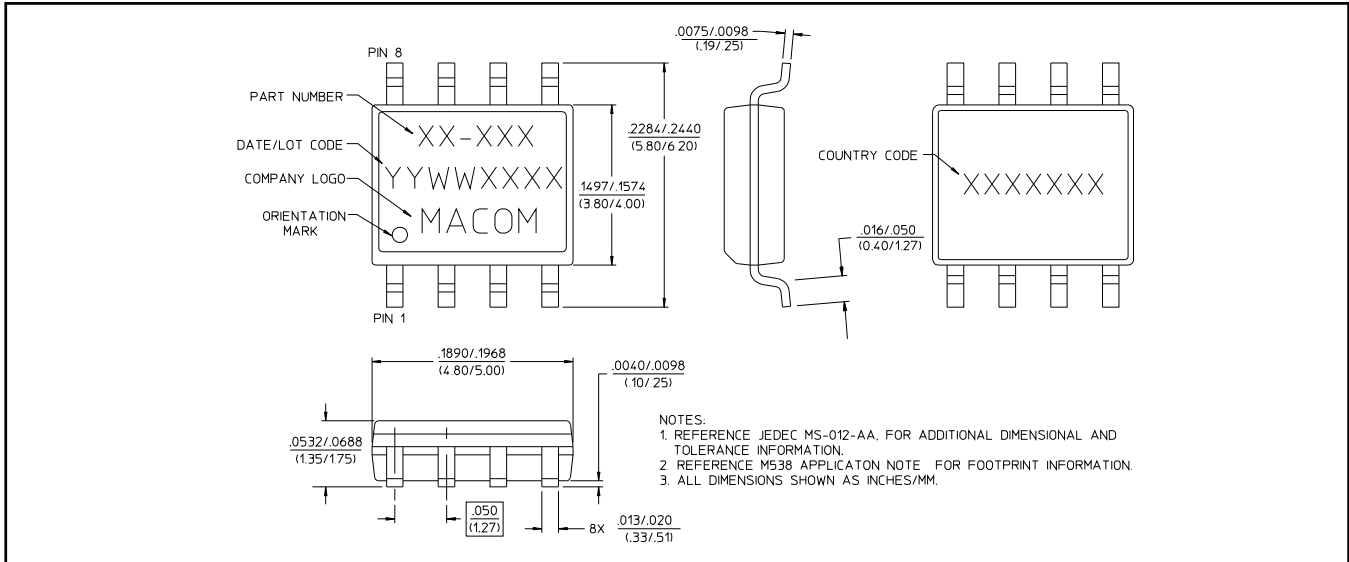
Noise Figure



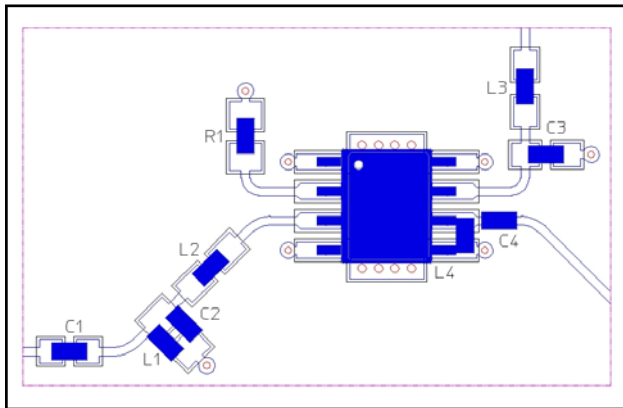
Output IP3



SO-8



Recommended PCB Configuration



Cross Section View

